

DESCRIPTION

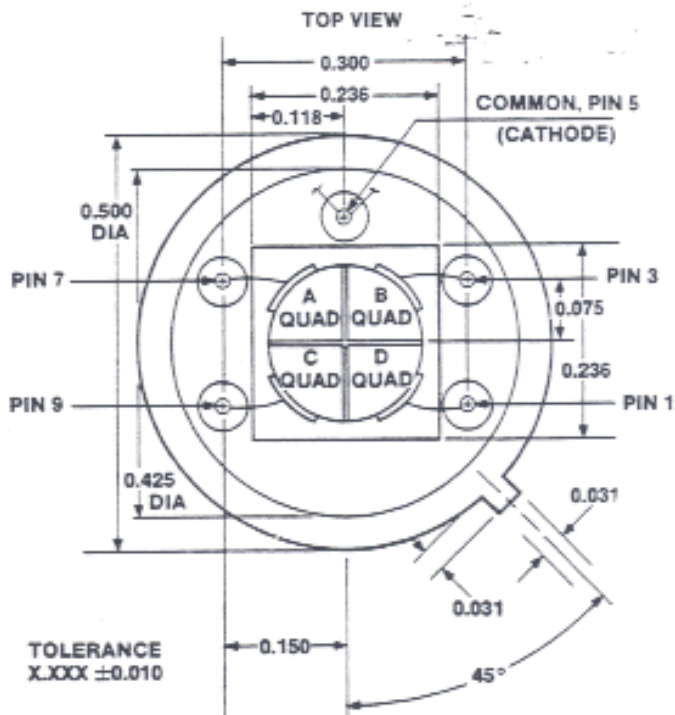
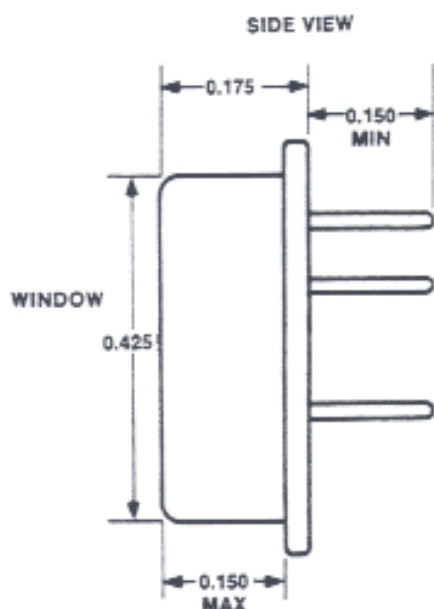
The TOX 9101 is an N-Type quadrant silicon photodiode with quadrant separation of 0.0254 mm (0.001 inch). These photodiodes are typically used as position sensors for applications such as optical tracking, optical alignment, and angular displacement.

ABSOLUTE MAXIMUM RATINGS

Storage temperature.....-65°C to +150°C
 Operating temperature.....-40°C to + 85°C
 Reverse voltage.....25° V

FEATURES

- High responsivity at 900 nm
- 5 Lead TO-8 hermetic package
- Cathode in electrical contact with case
- Active area 0.197 inch diameter



ELECTRO-OPTICAL CHARACTERISTICS (T_{CASE} = 25 C UNLESS OTHERWISE SPECIFIED)

PARAMETER	TEST CONDITIONS	SYMBOL	MIN	TYP	MAX	UNITS
Breakdown Voltage	I _R = 10 ¼A	BV _R	25			V
Dark Current (Per Quadrant)	V _R =10 V	I _D		20	100	nA
Responsivity	V _R = 1.5 V, » = 900 nm	R _e	0.35	0.5		A/W
Capacitance (Per Quadrant)	V _R = 0 V	C _T		50	100	pF
Uniformity	V _R = 1.5 V, » = 900 nm			5	7	%
Crosstalk	V _R = 1.5 V, » = 900 nm .			1	2	%

